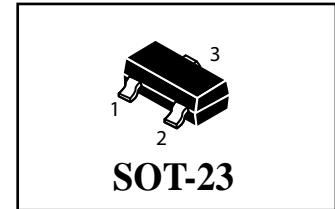
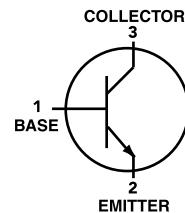


NPN General Purpose Transistors

 **Lead(Pb)-Free**


MAXIMUM RATINGS(T_a=25°C)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	50	V
Collector-Base Voltage	V _{CBO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Collector Current - Continuous	I _C	150	mA
Total Device Dissipation FR-5 Board T _A =25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate, TA=25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	417	°C/W
Junction Temperature	T _j	-55 to +150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector Cutoff Current $V_{CB} = 60V, I_E = 0$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current $V_{EB} = 5V, I_C = 0$	I_{EBO}	-	-	0.1	μA

ON CHARACTERISTICS

Collector-Emitter Saturation Voltage $I_C = 100mA, I_B = 10mA$	$V_{CE(sat)}$	-	0.15	0.3	V
Base-Emitter Saturation Voltage $I_C = 100mA, I_B = 10mA$	$V_{BE(sat)}$	-	0.86	1.0	V
Base-Emitter On Voltage $I_C = 1mA, V_{CE}=6.0V$	V_{BE}	0.55	0.62	0.65	V
DC Current Transfer Ration $V_{CE} = 6V, I_C = 1mA$	h_{FE}	120	-	560	

SMALL-SIGNAL CHARACTERISTICS

Transition frequency $V_{CE} = 6V, I_C = 10mA$	f_T	-	250	-	MHz
Output Capacitance($V_{CE} = 6V, I_E=0, f=1.0MHz$)	C_{ob}	-	3	-	Pf

CLASSIFICATION h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	L5	L6	L7

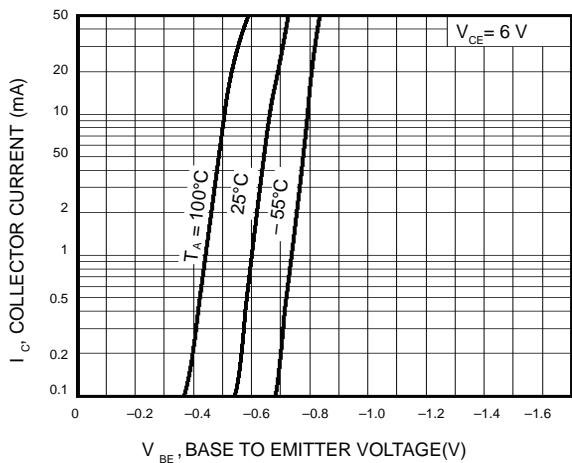


Fig.1 Grounded emitter propagation characteristics

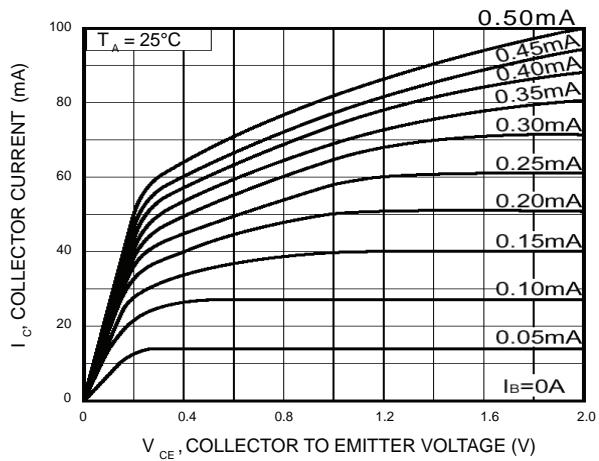


Fig.2 Grounded emitter output characteristics(I)

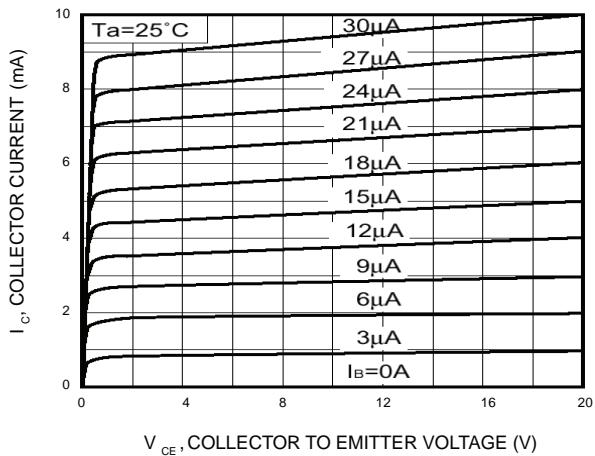


Fig.3 Grounded emitter output characteristics(II)

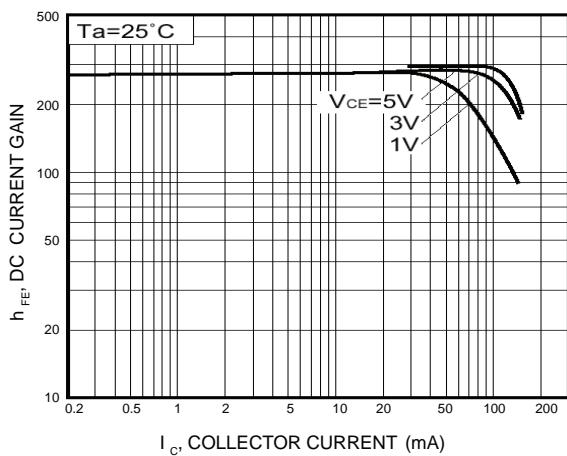


Fig.4 DC current gain vs. collector current (h_{FE})

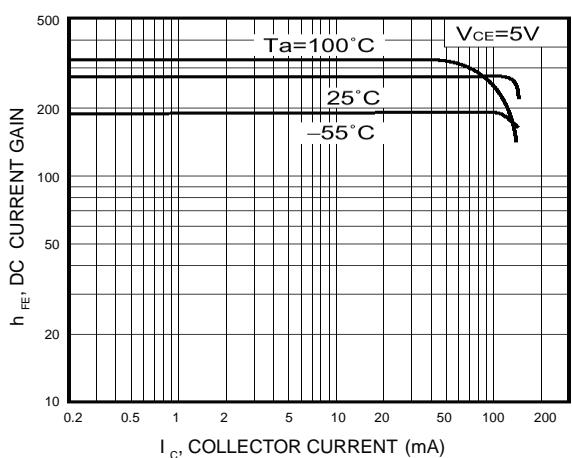


Fig.5 DC current gain vs. collector current (h_{FE})

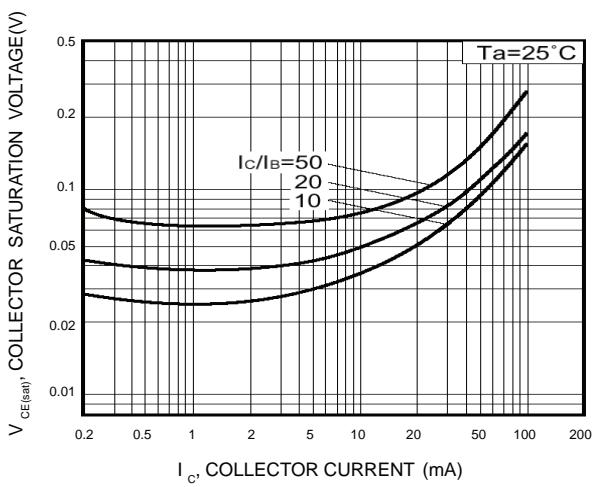


Fig.6 Collector-emitter saturation voltage vs. collector current

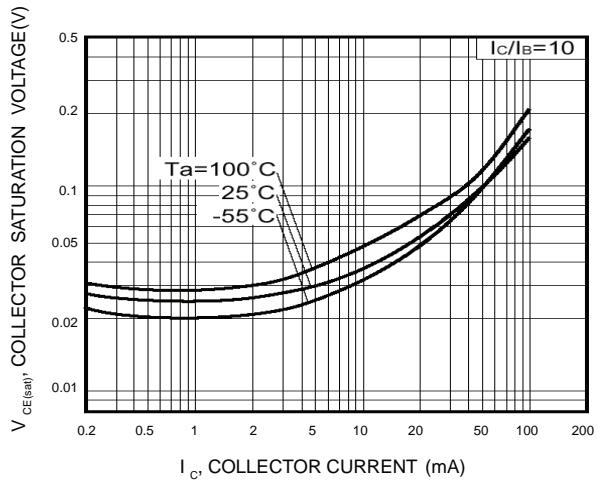


Fig.7 Collector-emitter saturation voltage vs. collector current (I)

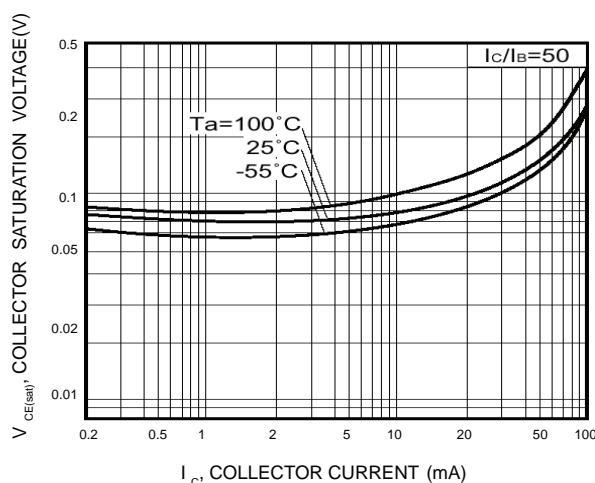


Fig.8 Collector-emitter saturation voltage vs. collector current (II)

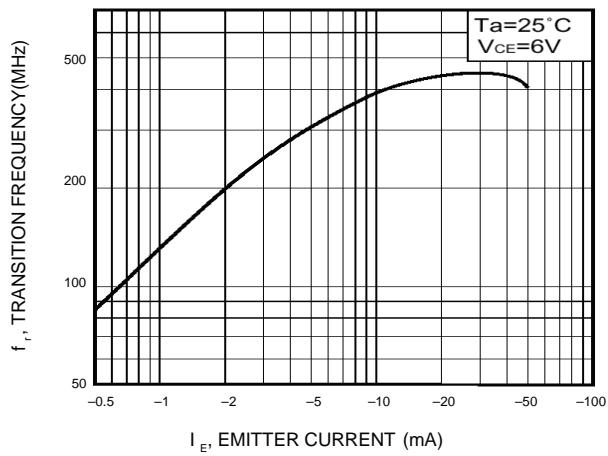


Fig.9 Gain bandwidth product vs. emitter current

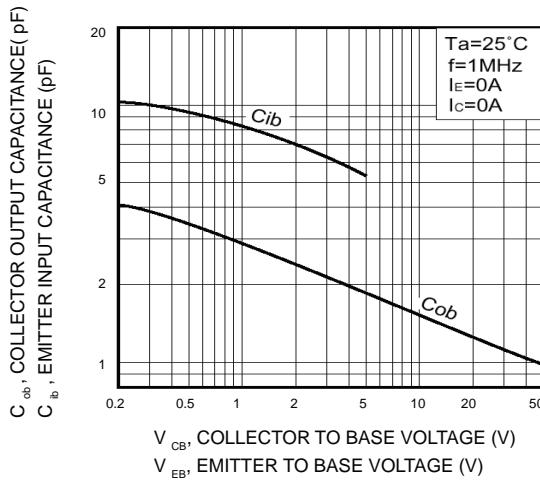


Fig.10 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

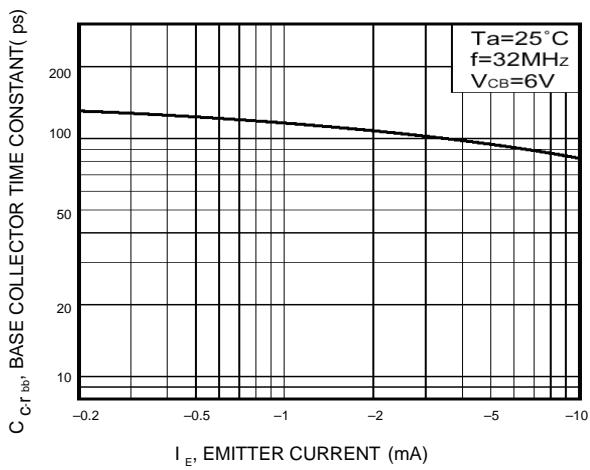
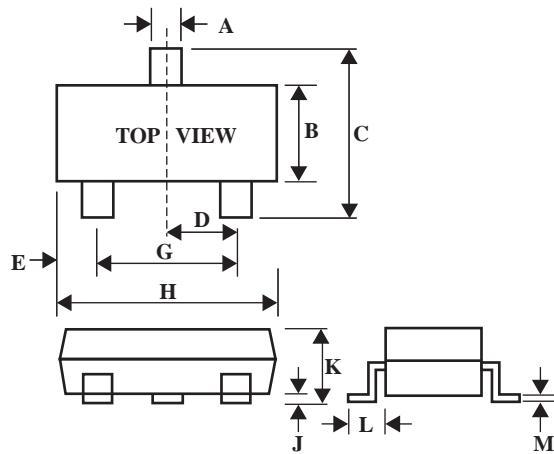


Fig.11 Base-collector time constant vs. emitter current

SOT-23 Outline Dimension



SOT-23		
Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25